

SII200S12

SPT IGBT Modules

Characteristics

T_c = 25°C, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _c = 6mA	4.8	5.5	6.45	V
I _{CES}	V _{GE} = 0; V _{CE} = V _{CES} ; T _j = 25(125)°C		0.2	0.6	mA
V _{CE(TO)}	T _j = 25(125)°C		1(0.9)	1.15(1.05)	V
r _{CE}	V _{GE} = 15V, T _j = 25(125)°C		6(8)	8(10)	mΩ
V _{CE(sat)}	I _c = 150A; V _{GE} = 15V; chip level		1.9(2.1)	2.35(2.55)	V
C _{ies}	under following conditions		13		nF
C _{oes}	V _{GE} = 0, V _{CE} = 25V, f = 1MHz		2		
C _{res}			2		
L _{CE}				20	nH
R _{CC+EE'}	res., terminal-chip T _c = 25(125)°C		0.35(0.5)		mΩ
t _{d(on)}	under following conditions: V _{CC} = 600V, I _c = 150A		125		ns
t _r	R _{Gon} = R _{Goff} = 7 Ω; T _j = 125°C		50		ns
t _{d(off)}	V _{GE} = ± 15V		620		ns
t _f			55		ns
E _{on} (E _{off})			18(15)		mJ
Inverse Diode under following conditions:					
V _F = V _{EC}	I _F = 150A; V _{GE} = 0V; T _j = 25(125)°C		2(1.8)	2.5	V
V _(TO)	T _j = 25(125)°C		1.1	1.2	V
r _T	T _j = 25(125)°C		6	8.7	mΩ
I _{RRM}	I _F = 150A; T _j = 125°C		190		A
Q _{rr}	di/dt = 4800A/us		24		uC
E _{rr}	V _{GE} = V		8		mJ
Thermal Characteristics					
R _{th(j-c)}	per IGBT			0.095	K/W
R _{th(j-c)D}	per Inverse Diode			0.25	K/W
R _{th(c-s)}	per module			0.038	K/W
Mechanical Data					
M _s	to heatsink M6	3		5	Nm
M _t	to terminals M6	2.5		5	Nm
w				325	g